山东迪一电子科技有限公司



1N4001 THRU 1N4007 险



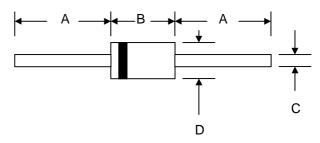
1.0A SILICON RECTIFIER

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.35 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-41							
Dim	Min	Max					
Α	25.4	—					
В	4.06	5.21					
С	0.71	0.864					
D	2.00	2.72					
All Dimensions in mm							

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	1N 4001	1N 4002	1N 4003	1N 4004	1N 4005	1N 4006	1N 4007	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) $@T_A = 75^{\circ}C$	lo	1.0						A	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	30					A		
Forward Voltage $@I_F = 1.0A$	VFM	1.0					V		
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Iгм	5.0 50						μA	
Typical Junction Capacitance (Note 2)	Cj	15					pF		
Typical Thermal Resistance Junction to Ambient (Note 1)	R ∂ JA	50				K/W			
Operating Temperature Range	Tj	-65 to +150					°C		
Storage Temperature Range	Тѕтс	-65 to +150					°C		

*Glass passivated forms are available upon request

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

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